

IN THE SPECIFICATION:

Please delete the second paragraph on page 4 in its entirety and substitute therefor the following substitute paragraph. Attached hereto is a marked-up copy of the substitute paragraph.

Q --Accordingly, it is expected that a crystallization temperature can be lowered by introducing crystal nuclei more positively. In order to confirm an effect of introducing crystal nuclei, the following experiment was tried. That is, a thin film of a different metal in a very small amount was beforehand formed on a substrate, then an amorphous silicon thin film was formed on the different metal film, and then heat-crystallization was conducted on the amorphous silicon thin film. As a result, it was proven that the crystallization temperature was lowered when thin films of some different kinds of metal were beforehand formed on the substrate, and it was expected that crystal growth using such a metal as crystal nuclei had conducted. Accordingly, a more detailed mechanism for plural kinds of impurity metal which could lower the crystallization temperature was studied.--

REMARKS

Applicant would like to thank the Examiner for the consideration given the above-identified application. The Examiner's Office Action of **October 31, 2001** has been received and its contents carefully noted. Concurrently filed herewith is a *Request for a One (1) Month Extension of Time* that extends the shortened statutory period for response until February 3, 2002. Accordingly, Applicant respectfully submits that this response is timely filed and fully responsive to the Office Action.

Claim 1 was pending in this application. Please note, however, that a Preliminary Amendment canceling claim 1 and adding new claims 2-23 was filed October 15, 2001,